HEF4518B

Dual BCD counter

Rev. 7 — 21 November 2011

Product data sheet

1. General description

The HEF4518B is a dual 4-bit internally synchronous BCD counter. The counter has an active HIGH clock input (nCP0) and an active LOW clock input (nCP1), buffered outputs from all four bit positions (nQ0 to nQ3) and an active HIGH overriding asynchronous master reset input (nMR). The counter advances on either the LOW-to-HIGH transition of the nCP0 input if nCP1 is HIGH or the HIGH-to-LOW transition of the nCP1 input if nCP0 is LOW. Either nCP0 or nCP1 may be used as the clock input to the counter and the other clock input may be used as a clock enable input. A HIGH on nMR resets the counter (nQ0 to nQ3 = LOW) independent of nCP0, nCP1. Schmitt trigger action in the clock input makes the circuit highly tolerant of slower clock rise and fall times.

It operates over a recommended V_{DD} power supply range of 3 V to 15 V referenced to V_{SS} (usually ground). Unused inputs must be connected to V_{DD} , V_{SS} , or another input.

2. Features and benefits

- Tolerant of slow clock rise and fall times
- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- Specified from -40 °C to +85 °C
- Complies with JEDEC standard JESD 13-B

3. Applications

- Multistage synchronous counting
- Multistage asynchronous counting
- Frequency dividers

4. Ordering information

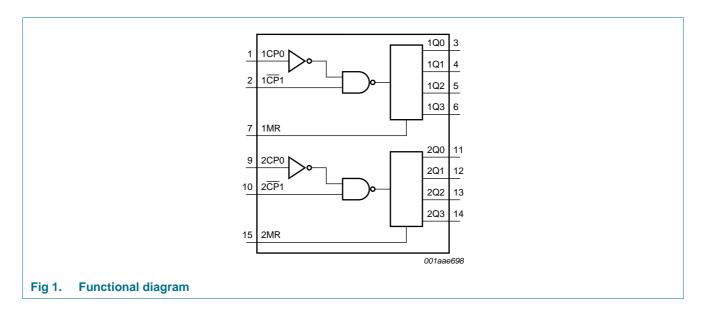
Table 1. Ordering information

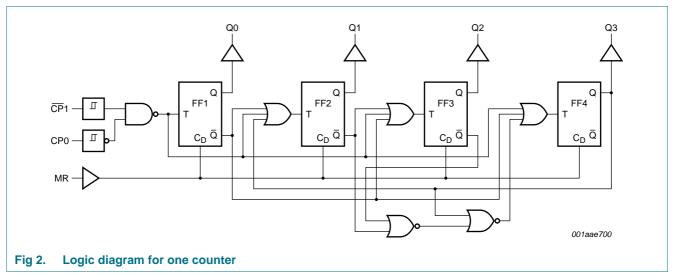
All types operate from -40 °C to +85 °C

Type number	Package		
	Name	Description	Version
HEF4518BP	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
HEF4518BT	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1



5. Functional diagram

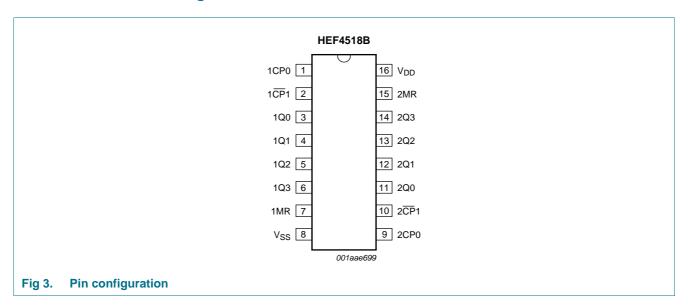




Dual BCD counter

6. Pinning information

6.1 Pinning



6.2 Pin description

Table 2. Pin description

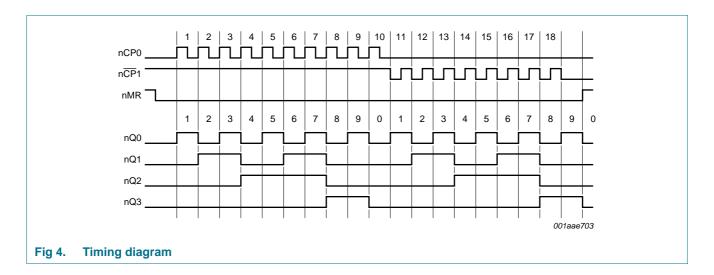
Symbol	Pin	Description
1CP0, 2CP0	1, 9	clock input (LOW-to-HIGH triggered)
1CP1, 2CP1	2, 10	clock input (HIGH-to-LOW triggered)
1Q0, 2Q0	3, 11	output
1Q1, 2Q1	4, 12	output
1Q2, 2Q2	5, 13	output
1Q3, 2Q3	6, 14	output
1MR, 2MR	7, 15	master reset input
V_{DD}	16	supply voltage
V _{SS}	8	ground supply voltage

7. Functional description

Table 3. Function table[1]

nCP0	nCP1	nMR	Mode
\uparrow	Н	L	counter advances
L	\downarrow	L	counter advances
\downarrow	Χ	L	no change
X	↑	L	no change
\uparrow	L	L	no change
Н	\downarrow	L	no change
X	Χ	Н	nQ0 to nQ3 = LOW

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; ↑ = positive-going transition; ↓ = negative-going transition.



Dual BCD counter

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DD}	supply voltage		-0.5	+18	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{DD} + 0.5 \text{ V}$	-	±10	mA
VI	input voltage		-0.5	$V_{DD} + 0.5$	V
I _{OK}	output clamping current	V_{O} < -0.5 V or V_{O} > V_{DD} + 0.5 V	-	±10	mA
I _{I/O}	input/output current		-	±10	mA
I_{DD}	supply current		-	50	mA
T _{stg}	storage temperature		-65	+150	°C
T _{amb}	ambient temperature		-40	+85	°C
P _{tot}	total power dissipation	DIP16 package	<u>[1]</u> -	750	mW
		SO16 package	[2] _	500	mW
Р	power dissipation	per output	-	100	mW

^[1] For DIP16 package: P_{tot} derates linearly with 12 mW/K above 70 °C.

9. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DD}	supply voltage		3	-	15	V
VI	input voltage		0	-	V_{DD}	V
T _{amb}	ambient temperature	in free air	-40	-	+85	°C
Δt/ΔV	input transition rise and fall rate	$V_{DD} = 5 V$	-	-	3.75	μs/V
		V _{DD} = 10 V	-	-	0.5	μs/V
		V _{DD} = 15 V	-	-	0.08	μs/V

10. Static characteristics

Table 6. Static characteristics

 $V_{SS} = 0 \ V$; $V_I = V_{SS}$ or V_{DD} unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	T _{amb} =	-40 °C	T _{amb} = 25 °C		T _{amb} = 85 °C		Unit
				Min	Max	Min	Max	Min	Max	
V_{IH}	HIGH-level input voltage	l _O < 1 μA	5 V	3.5	-	3.5	-	3.5	-	V
			10 V	7.0	-	7.0	-	7.0	-	V
			15 V	11.0	-	11.0	-	11.0	-	V
V_{IL}	LOW-level input voltage	I _O < 1 μA	5 V	-	1.5	-	1.5	-	1.5	V
			10 V	-	3.0	-	3.0	-	3.0	V
			15 V	-	4.0	-	4.0	-	4.0	V

^[2] For SO16 package: Ptot derates linearly with 8 mW/K above 70 °C.

Dual BCD counter

 Table 6.
 Static characteristics ...continued

 $V_{SS} = 0 \ V$; $V_I = V_{SS}$ or V_{DD} unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	T _{amb} =	–40 °C	T _{amb} =	25 °C	T _{amb} =	= 85 °C	Unit
				Min	Max	Min	Max	Min	Max	
V_{OH}	HIGH-level output voltage	$ I_{O} < 1 \mu A$	5 V	4.95	-	4.95	-	4.95	-	V
			10 V	9.95	-	9.95	-	9.95	-	V
			15 V	14.95	-	14.95	-	14.95	-	V
V _{OL}	LOW-level output voltage	$ I_{O} < 1 \mu A$	5 V	-	0.05	-	0.05	-	0.05	V
			10 V	-	0.05	-	0.05	-	0.05	V
			15 V	-	0.05	-	0.05	-	0.05	V
I _{OH}	HIGH-level output current	V _O = 2.5 V	5 V	-	-1.7	-	-1.4	-	-1.1	mΑ
		V _O = 4.6 V	5 V	-	-0.52	-	-0.44	-	-0.36	mΑ
		V _O = 9.5 V	10 V	-	-1.3	-	-1.1	-	-0.9	mΑ
		V _O = 13.5 V	15 V	-	-3.6	-	-3.0	-	-2.4	mΑ
I _{OL}	LOW-level output current	$V_0 = 0.4 \text{ V}$	5 V	0.52	-	0.5	-	0.36	-	mΑ
		V _O = 0.5 V	10 V	1.3	-	1.1	-	0.9	-	mΑ
		V _O = 1.5 V	15 V	3.6	-	3.0	-	2.4	-	mΑ
I _I	input leakage current	$V_{DD} = 15 \text{ V}$	15 V	-	±0.3	-	±0.3	-	±1.0	μΑ
I _{DD}	supply current	I _O = 0 A	5 V	-	20	-	20	-	150	μΑ
			10 V	-	40	-	40	-	300	μΑ
			15 V	-	80	-	80	-	600	μΑ
Cı	input capacitance		-	-	-	-	7.5	-	-	pF

11. Dynamic characteristics

Table 7. Dynamic characteristics

 $V_{SS} = 0 \text{ V; } T_{amb} = 25 \text{ °C; for test circuit see } \underline{Figure 6}; unless otherwise specified.$

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula	Min	Тур	Max	Unit
t_{PHL}	HIGH to LOW	nCP0, n $\overline{CP1}$ to nQn;	5 V 🔼	93 ns + (0.55 ns/pF)C _L	-	120	240	ns
	propagation delay	see Figure 5	10 V	44 ns + (0.23 ns/pF)C _L	-	55	110	ns
			15 V	$32 \text{ ns} + (0.16 \text{ ns/pF})C_L$	-	40	80	ns
		nMR to nQn; see <u>Figure 5</u>	5 V	48 ns + $(0.55 \text{ ns/pF})C_L$	-	75	150	ns
			10 V	24 ns + (0.23 ns/pF)C _L	-	35	70	ns
			15 V	17 ns + (0.16 ns/pF)C _L	-	25	50	ns
t _{PLH}	LOW to HIGH	nCP0, nCP1 to nQn; see Figure 5	5 V 🔼	93 ns + (0.55 ns/pF)C _L	-	120	240	ns
	propagation delay		10 V	44 ns + (0.23 ns/pF)C _L	-	55	110	ns
			15 V	32 ns + (0.16 ns/pF)C _L	-	40	80	ns
t _t	transition time	nQn; see Figure 5	5 V [1]	10 ns + (1.00 ns/pF)C _L	-	60	120	ns
			10 V	9 ns + (0.42 ns/pF)C _L	-	30	60	ns
			15 V	6 ns + (0.28 ns/pF)C _L	-	20	40	ns

Dual BCD counter

 Table 7.
 Dynamic characteristics ...continued

 $V_{SS} = 0 \text{ V}$; $T_{amb} = 25 \,^{\circ}\text{C}$; for test circuit see <u>Figure 6</u>; unless otherwise specified.

Symbol	Parameter	Conditions	V_{DD}	Extrapolation formula	Min	Тур	Max	Unit
t _W	pulse width	nCP0 input LOW;	5 V		60	30	-	ns
		minimum width;	10 V		30	15	-	ns
		see <u>Figure 5</u>	15 V		20	10	-	ns
		nCP1 input HIGH;	5 V		60	30	-	ns
		minimum width;	10 V		60 30 - 30 15 - 20 10 - 60 30 - 30 15 - 20 10 - 30 15 - 20 10 - 30 15 - 20 10 - 16 8 - 50 25 - 30 15 - 20 10 - 50 25 - 30 15 - 20 10 - 50 25 - 30 15 - 20 10 - 50 25 - 30 15 - 20 10 - 50 25 - 30 15 - 20 10 - 50 25 - 30 15 - 20 10 -	-	ns	
		see <u>Figure 5</u>	15 V		20	10	- r - r - r - r - r - r - r - r - r - r	ns
		nMR input HIGH;	5 V		30	15	-	ns
		minimum width;	10 V		20	10	-	ns
		see <u>Figure 5</u>	15 V		16	8	-	ns
t _{rec}	recovery time	nMR input; see Figure 5	5 V		50	25	-	ns
			10 V		30	15	-	ns
			15 V		20	10	-	ns
t _{su}	set-up time	nCP0 to nCP1;	5 V		50	25	-	ns
		see <u>Figure 5</u>	10 V		30	15	-	ns
			15 V		20	10	-	ns
		nCP1 to nCP0;	5 V		50	25	-	ns
		see <u>Figure 5</u>	10 V		30	15	-	ns
			15 V		20	10	-	ns
f _{max}	maximum	nCP0, nCP1;	5 V		8	16	-	MHz
	maximum frequency	see <u>Figure 5</u>	10 V		15	30	-	MHz
			15 V		20	40	-	MHz

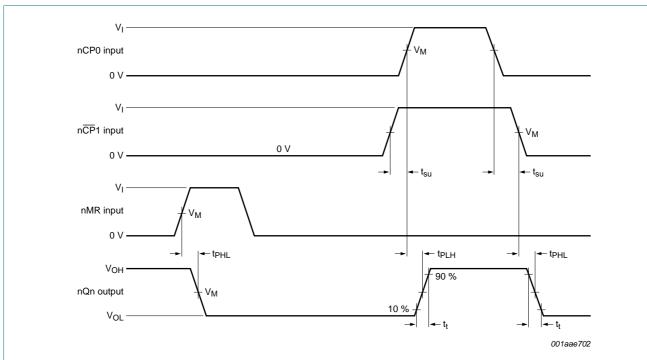
^[1] The typical values of the propagation delay and transition times are calculated from the extrapolation formulas shown (C_L in pF).

Table 8. Dynamic power dissipation P_D

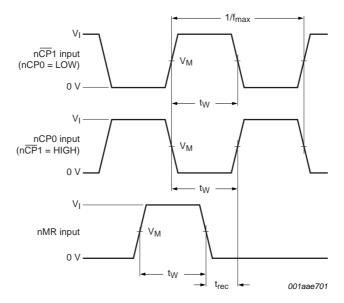
 P_D can be calculated from the formulas shown. $V_{SS} = 0$ V; $t_r = t_f \le 20$ ns; $T_{amb} = 25$ °C.

Symbol	Parameter	V_{DD}	Typical formula for P_D (μ W)	Where:
P_D	dynamic power	5 V	$P_D = 750 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2$	f _i = input frequency in MHz;
	dissipation	10 V	$P_D = 3300 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2$	f _o = output frequency in MHz;
		15 V	$P_D = 8000 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2$	C_L = output load capacitance in pF;
				V_{DD} = supply voltage in V;
				$\Sigma(f_0 \times C_L)$ = sum of the outputs.

12. Waveforms

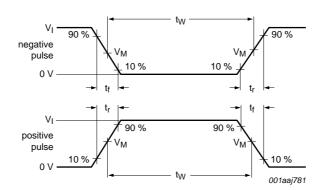


a. nCP0 and nCP1 set-up times, propagation delays and output transition times

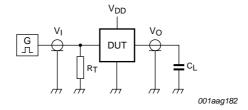


b. nMR recovery time, minimum nCP0, nCP1, and nMR pulse widths and maximum frequency
 Measurement points are given in table <u>Table 9</u>.
 The logic levels V_{OH} and V_{OL} are typical output voltage levels that occur with the output load.

Fig 5. Waveforms showing measurements for switching times



a. Input waveforms



b. Test circuit

Test data is given in Table 9.

Definitions for test circuit:

DUT = Device Under Test;

 C_L = Load capacitance including jig and probe capacitance;

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

Fig 6. Test circuit for switching times

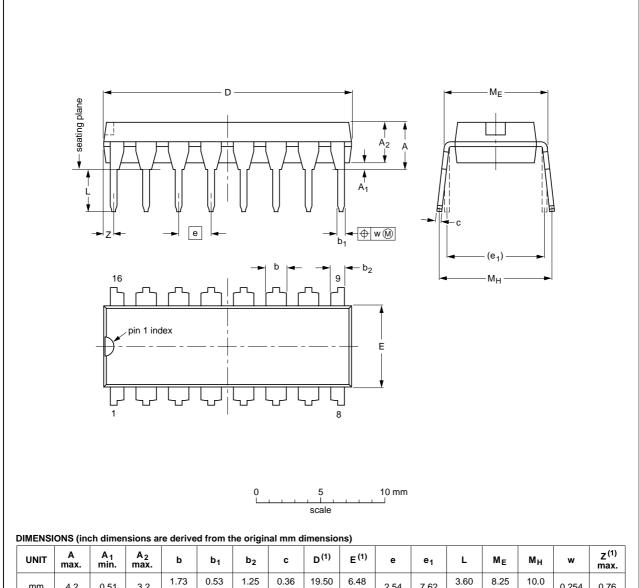
Table 9. Measurement points and test data

Supply voltage	Input			Load
	V _I	V _M	t _r , t _f	CL
5 V to 15 V	V_{DD}	0.5V _I	≤ 20 ns	50 pF

13. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4



UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	b ₂	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	Мн	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.03

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

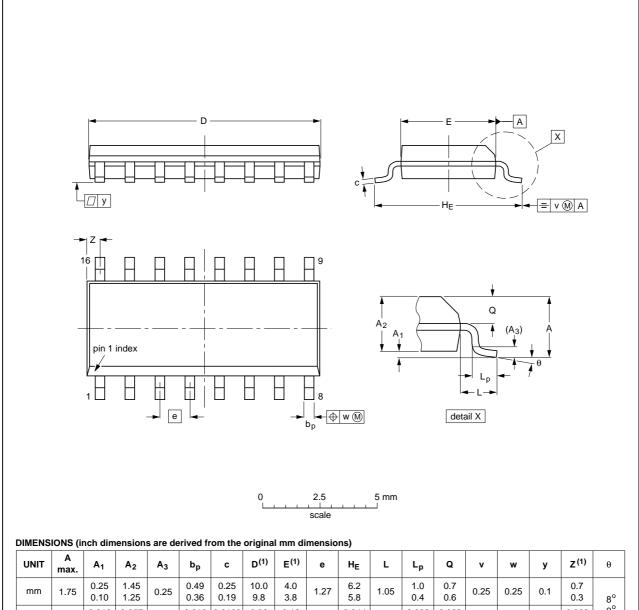
OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT38-4						95-01-14 03-02-13	

Fig 7. Package outline SOT38-4 (DIP16)

HEF4518B

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	U	D ⁽¹⁾	E ⁽¹⁾	е	HE	٦	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01	1	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016		0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

	REFER	EUROPEAN	ISSUE DATE			
IEC	JEDEC	JEDEC JEITA		PROJECTION	IOOUL DATE	
076E07	MS-012				99-12-27 03-02-19	
_		IEC JEDEC		IEC JEDEC JEITA	IEC JEDEC JEITA PROJECTION	

Fig 8. Package outline SOT109-1 (SO16)

HEF4518B

Dual BCD counter

14. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4518B v.7	20111121	Product data sheet	-	HEF4518B v.6
Modifications:	• <u>Table 6</u> : I _{OI} -	minimum values changed to	o maximum	
	• Figure 6: ad	dded "DUT = Device Under 1	Test"	
HEF4518B v.6	20091210	Product data sheet	-	HEF4518B v.5
HEF4518B v.5	20090727	Product data sheet	-	HEF4518B v.4
HEF4518B v.4	20090703	Product data sheet	-	HEF4518B_CNV v.3
HEF4518B_CNV v.3	19950101	Product specification	-	HEF4518B_CNV v.2
HEF4518B_CNV v.2	19950101	Product specification	-	-

Dual BCD counter

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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HEF4518B

Dual BCD counter

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HEF4518B NXP Semiconductors Dual BCD counter

17. Contents

1	General description 1
2	Features and benefits 1
3	Applications
4	Ordering information
5	Functional diagram 2
6	Pinning information
6.1	Pinning
6.2	Pin description
7	Functional description 4
8	Limiting values 5
9	Recommended operating conditions 5
10	Static characteristics 5
11	Dynamic characteristics 6
12	Waveforms
13	Package outline
14	Revision history
15	Legal information
15.1	Data sheet status
15.2	Definitions
15.3	Disclaimers
15.4	Trademarks14
16	Contact information
17	Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.